

Use-it or Lose-it: Wearout and Lifetime in Future Chip-Multiprocessors



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Introduction



- Moore's law scaling continues
 - Denard scaling ending
 - Power/performance trade-off driving core increases
 - Increasing core counts push complexity into interconnect
 - Interconnect becomes critical to CMP functionality

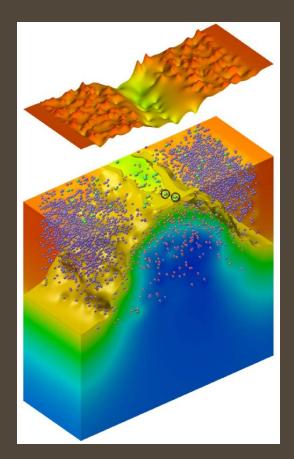


Intel Single-Chip Cloud Computer 48-core chip-multiprocessor (CMP) 2011

Moore's Law and Reliability



- ITRS: per-transistor failure rate must decrease 10X by 2023
 - "Manufacturable solutions *not* known"
- Failure mechanisms with time and use
 - Hot Carrier Injection (HCI)
 - Negative Bias Temperature Instability (NBTI)
- Transistor wear effects
 - Transistors slow w/ wear
 - Data dependent causes (roughly) inverse



Charge trapping in pMOSFET after NBTI induced stress. [Brown et al., IEEE Trans. Electron Devices 2010]

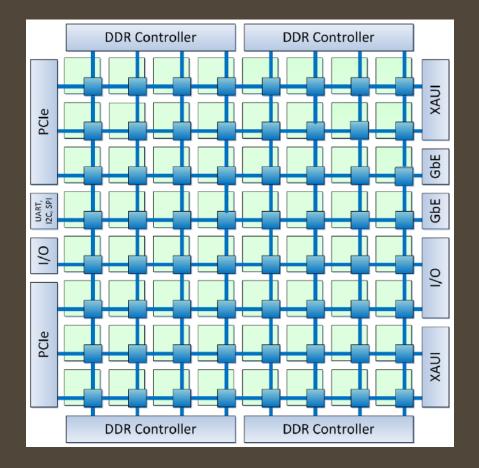


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• Each core accounts for less of system throughput



A 64-core Chip-Multiprocessor (CMP) with various peripherals interconnected via a 2-D Mesh

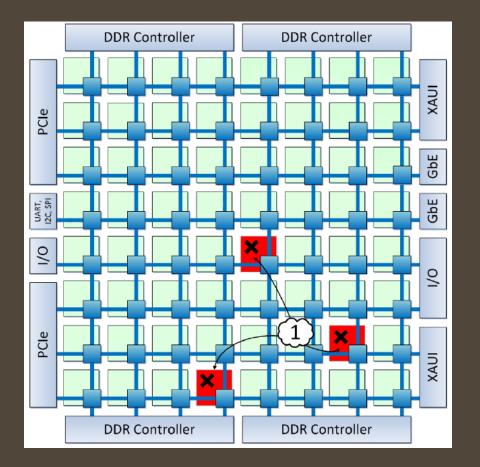


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• Increasing core counts

- Each core accounts for less of system throughput
- Core redundancy
 - Other cores can take over workload
 - Fault-tolerant task migration
 - Other micro-arch methods



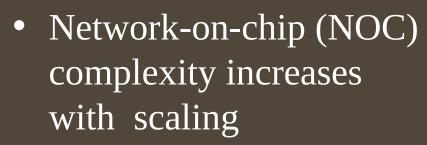


Scenario #1: Failure of three cores due to wearout, workload redistributed to other cores

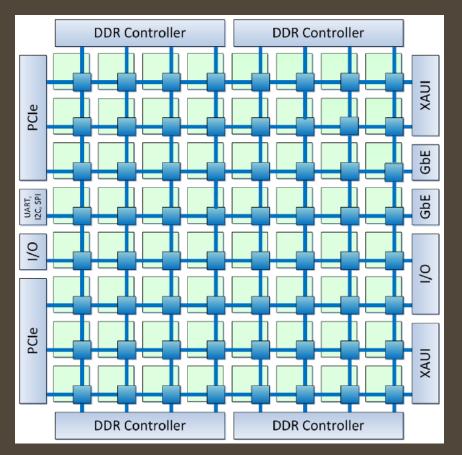


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• NoC critical to CMP operation

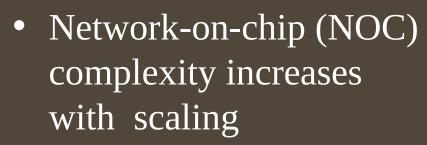


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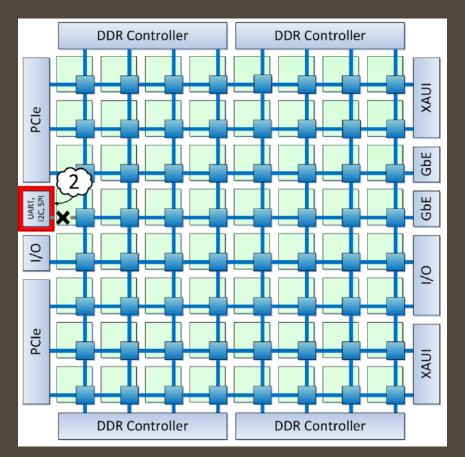


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• NoC critical to CMP operation

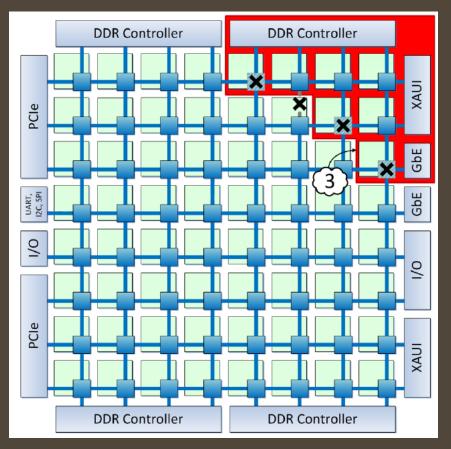


Scenario #2: A peripheral device disconnected from the CMP due to interconnect failure



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- Network-on-chip (NOC) complexity increases with scaling
- NoC critical to CMP operation

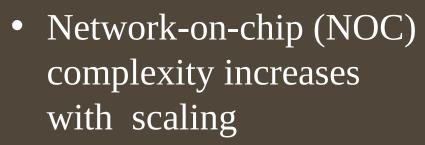


Scenario #3: Peripheral devices and entire NoC region disconnected from the network due to chained faults in links

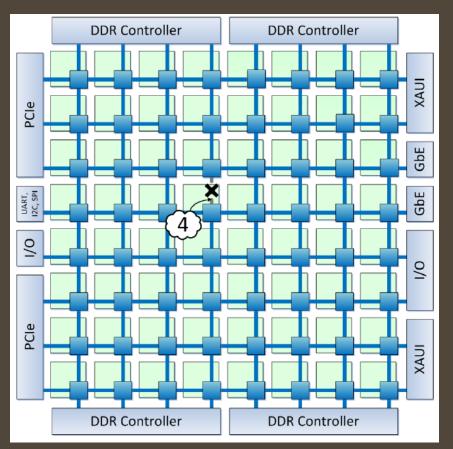


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• NoC critical to CMP operation

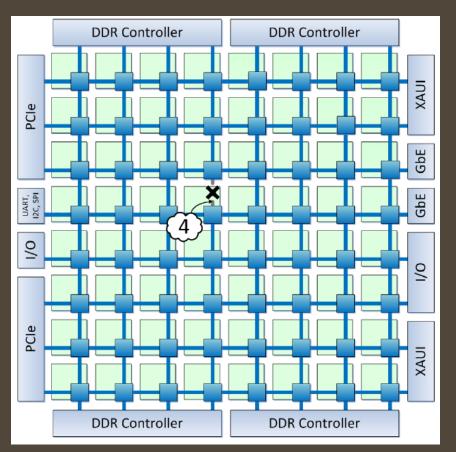


Scenario #4: A single link failure leading to routing deadlock



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- Network-on-chip (NOC) complexity increases with scaling
- NoC critical to CMP operation
- Single failure could incapacitate CMP!



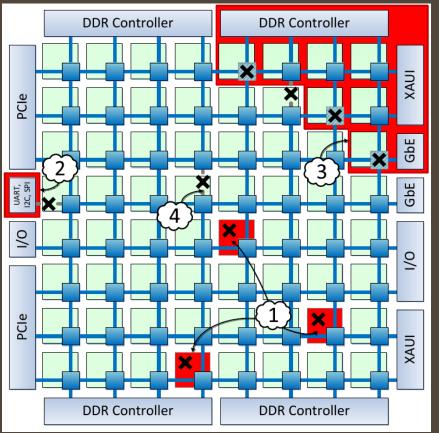
Scenario #4: A single link failure leading to routing deadlock



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Project goal:

- Develop techniques to mitigate wearout in the NoC
 - Analyze breakdown by mechanism
 - Characterize wear due to real workloads on routers and links
 - Develop wear-resistant router microarchitectures



A 64-core Chip-Multiprocessor (CMP) with various peripherals interconnected via a 2-D Mesh, all failure scenarios illustrated

Outline



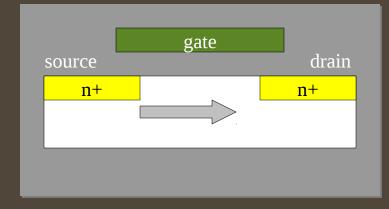
- Introduction
- Background
 - Failure mechanisms in modern CMOS
 - Hot Carrier Injection (HCI)
 - Negative Bias Temperature Instability (NBTI)
- Reliability characterization
- Wearout-resistant router microarchitecture
- Evaluation
- Conclusions

Failure mechanisms: Hot Carrier Injection (HCI)



• Cause:

- When current flows through channel
- Charge carrier gains sufficient energy to embed in gate oxide

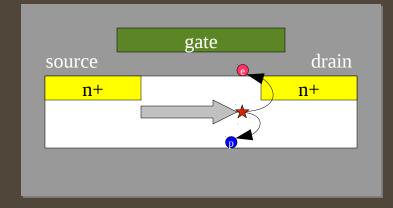


Failure mechanisms: Hot Carrier Injection (HCI)



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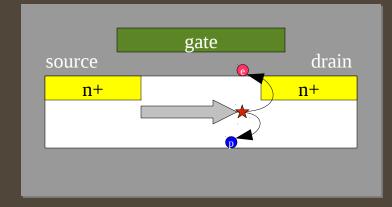


Failure mechanisms: Hot Carrier Injection (HCI)



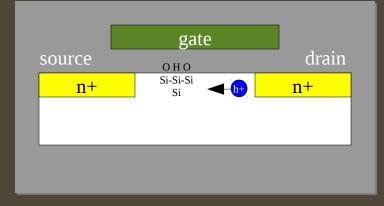
• Cause:

- When current flows through channel
- Charge carrier gains sufficient energy to embed in gate oxide
- Effect:
 - Shifts Vt
 - "Slows" transistor switching speed



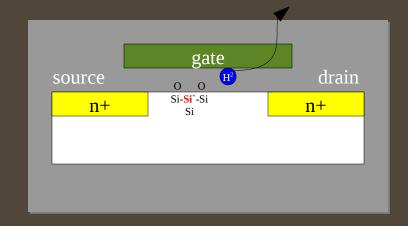


- Cause:
 - Hole induction breaks
 Si-H bonds at gate-oxide interface



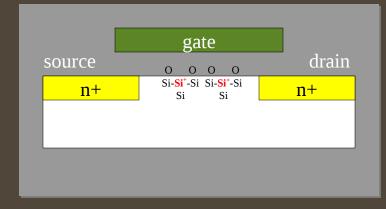


- Cause:
 - Hole induction breaks
 Si-H bonds at gate-oxide interface
 - H atoms form H² in oxide
 - H² diffuse to gate, trapping charge in gate oxide



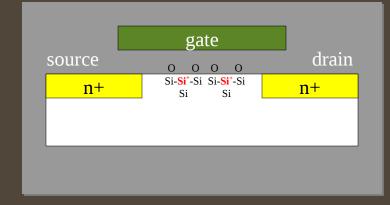


- Effect:
 - Shift in Vt
 - "Slows" transistor switching speed





- Effect:
 - Shift in Vt
 - "Slows" transistor switching speed
- Effect worsens w/ high-K dielectric
- Much worse in MuGFETs



Failure mechanisms: Summary



- Each mechanism occurs under different conditions
 - HCI proportional to current across channel
 - HCI increases with increased transistor activity factor
 - NBTI proportional to time gate held at 0V
 - NBTI increases with 0-skewed duty cycle
- Both mechanisms effect switching speed of transistor
 - Transistor does not "break" just slows down
 - Thus strongest impact on critical path
- Effect of usage on wear nearly opposite!
 - Increased activity \rightarrow Increased HCI
 - Lower duty cycle \rightarrow Increased NBTI

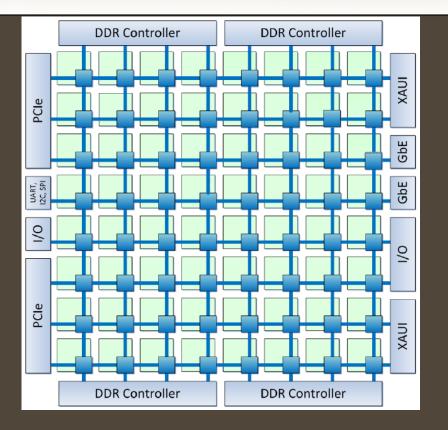
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Router Microarchitecture

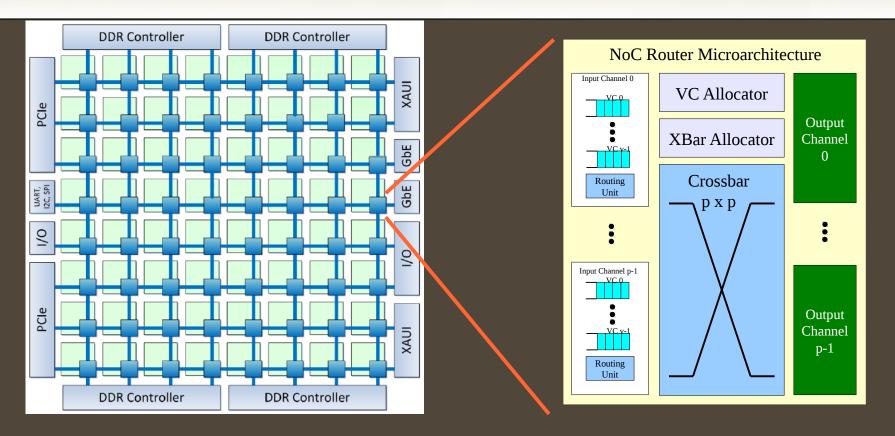




A 64-core Chip-Multiprocessor (CMP) with various peripherals interconnected via a 2-D Mesh

Router Microarchitecture



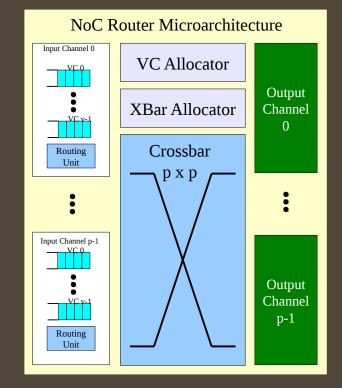


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Router Critical Path



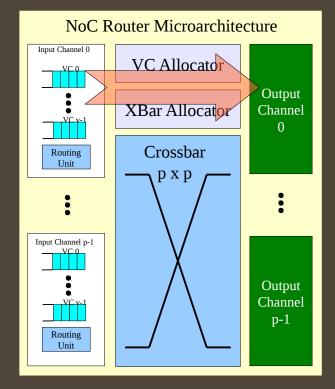
- HCI and NBTI slow transistors
- Wearout occurs first where timing critical
- Analyze critical path for susceptibility to wear



Router Critical Path



- NoC router critical path in 2nd pipeline stage
 - From input VC
 - Through VC and Xbar allocators
 - To 3rd stage pipeline latches
- Activity of wires along path correlated with injection rate of router
- Application dependent!

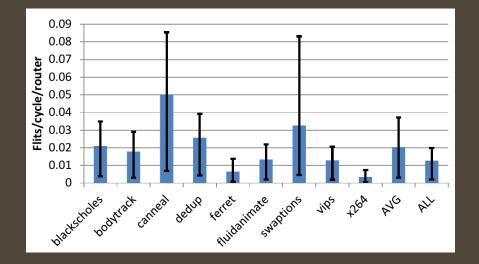


Router critical path typically lies through VC and Xbar allocation

CMP Workload Characterization



- Examined variance in per-router load
 - Incoming rate to each router individually
 - PARSEC workloads

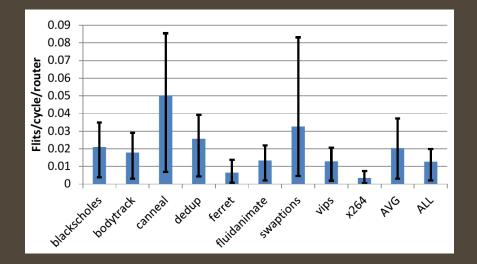


Load seen by each router under PARSEC suite benchmarks (incoming rate). Average (bar), minimum and maximum (whiskers).

CMP Workload Characterization



- Examined variance in per-router load
 - Incoming rate to each router individually
 - PARSEC workloads
- Great variance in load
 - Between applications
 - From router to router within network
- Implication: wearout is highly workload dependent



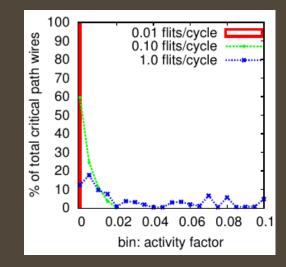
Load seen by each router under PARSEC suite benchmarks (incoming rate). Average (bar), minimum and maximum (whiskers).

Workload impact on wearout: HCI – Activity on critical path



Examined activity factor of router critical path to determine HCI impact

- Some sensitivity to injection rate
- Even for extreme injection rates, activity factor remains low



Activity factor histogram for critical path nodes within router, under random injection of varying rate. Critical path nodes defined as nodes on all paths with latency within 10% of clock period.

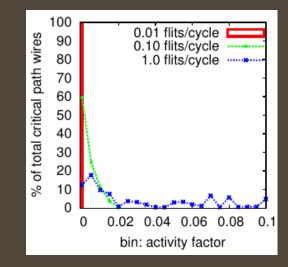
Workload impact on wearout: HCI – Activity on critical path



Examined activity factor of router critical path to determine HCI impact

- Some sensitivity to injection rate
- Even for extreme injection rates, activity factor remains low

Implication: Activity factor on critical path low, and insensitive to workload – HCI impact low



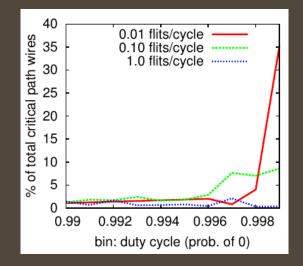
Activity factor histogram for critical path nodes within router, under random injection of varying rate. Critical path nodes defined as nodes on all paths with latency within 10% of clock period.

Workload impact on wearout: NBTI – Duty cycle on critical path



Examined duty cycle of router critical path to determine NBTI impact

- Duty cycle poor for a high percentage of critical path nodes
- Highly sensitive to injection rate
 - Duty cycle improves as injection rate increases



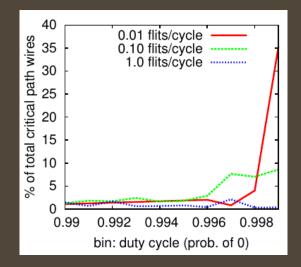
Duty cycle (fraction of time at 0) histogram for critical path nodes within router, under random injection of varying rate.

Workload impact on wearout: NBTI – Duty cycle on critical path



Examined duty cycle of router critical path to determine NBTI impact

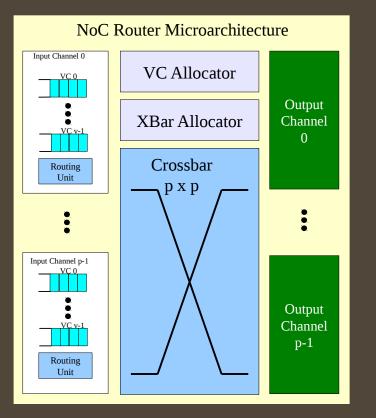
- Duty cycle poor for a high percentage of critical path nodes
- Highly sensitive to injection rate
 - Duty cycle improves as injection rate increases
- Implications:
 - NBTI induced wear is likely
 - NBTI stress inversely proportional to load!



Duty cycle (fraction of time at 0) histogram for critical path nodes within router, under random injection of varying rate.

Reliability characterization summary





- Wear is injection rate dependent along the critical path
- Low injection rates cause poor duty cycle and accelerated NBTI
- Critical path primarily concerned with VC and Xbar allocation

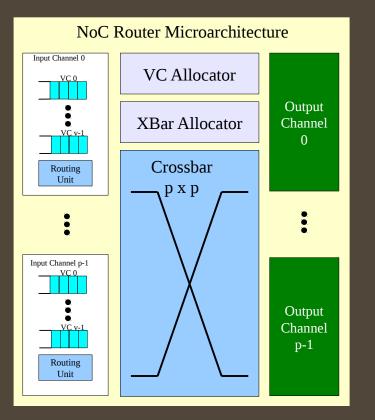
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- Introduction
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- Related work
- Reliability characterization
- Use it or Lose it: wearout-resistant router microarchitecture
- Evaluation
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Addressing wear in the NoC router





- Increasing injection rate artificially yields other problems
 - Power increases
 - HCI increases
 - Congestion
- Want to improve duty cycle w/o increasing activity factor

The Use it or Lose it router microarchitecture



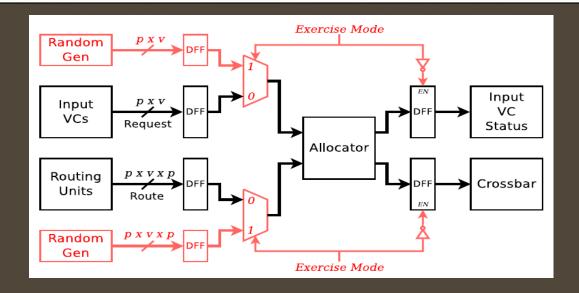
Use it or Lose it: Need mechanism to exercise critical path through the allocators or we will "lose" them

Goals:

- 1. Improve duty cycle by creating more time spent at "1"
- 2. Should not change state of router
- 3. Should not worsen critical path timing
- 4. Should not significantly increase activity factor
 - Power and HCI are activity factor dependent

The Use it or Lose it router microarchitecture





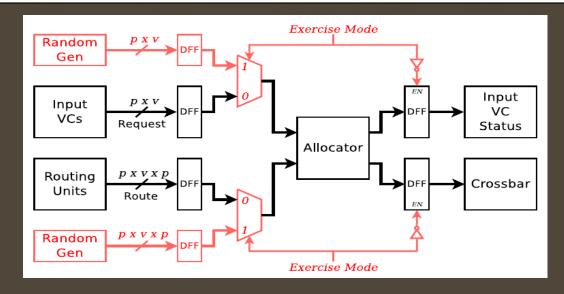
Create an "exercise mode" for critical path

1. Improve duty cycle by creating more time spent at "1"

- Inject random data into allocators
- Emulate higher injection rates
- Hit corner cases

The Use it or Lose it router microarchitecture

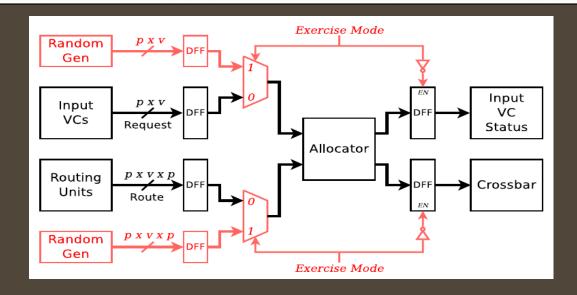




- 2. Should not change state of router
 - Only enabled when no packets ready in input FIFOs
 - Router state latches are disabled during exercise mode
- 3. Should not worsen critical path timing
 - Only one mux added to actual path
 - All vector generation and mode selection logic off critical path

The Use it or Lose it router microarchitecture





4. Should not significantly increase activity factor

- Only paths with poor duty cycle on critical path are modified
- Vector generator changes vector slowly, once every 128 cycles
- Minimal impact on router activity factor

Random Vector Generation



- ROM containing pre-generated random vectors
 - Low overhead
 - Examined range of ROM sizes
 - ROM sizes >16 produced little return
 - Examined range of ROM vector rotation periods
- Examined other methods to generate random vector (see paper)

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Implementation



- Baseline and Wear-resistant router synthesized in 45nm TSMC process tech

 Results scaled to 22nm
- Low overheads of technique
 - $-\sim 1\%$ increase in router power consumption
 - < 1% increase in router area

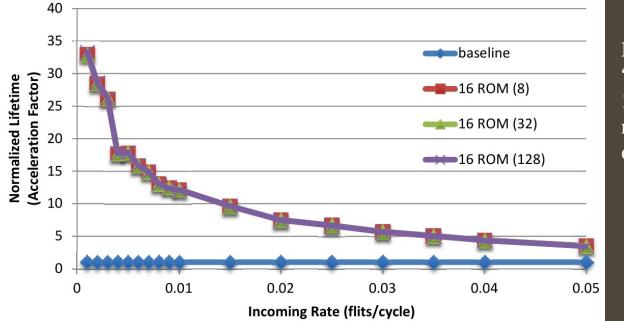




- Post-synth router models developed for Baseline and Wear-resistant
- Post-synth router models simulated under PARSEC-like workloads
 - 64-node, 2-D Mesh (8x8)
 - Five-port, three-stage, 2-D mesh router
 - Four-VCs per port, each four flits deep
- Activity factor and duty cycle of wires along router critical paths extracted

Results: Lifetime Increase Under Synthetic Workload





Notation: "16 ROM (8)": 16 entry ROM, rotated every 8 cycles.

Lifetime of *Use it or Lose it* router experiencing NBTI wear under various injection rates normalized against the baseline router.

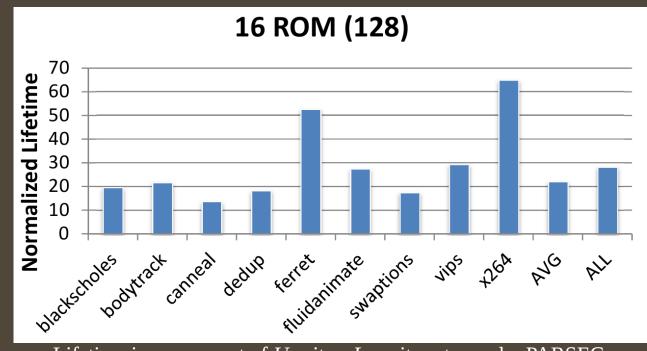
• Dramatic improvement in lifetime

- Improvement best at low loads when wear is worst

• Insensitive to rotation period

Results: Lifetime Increase Under PARSEC workloads





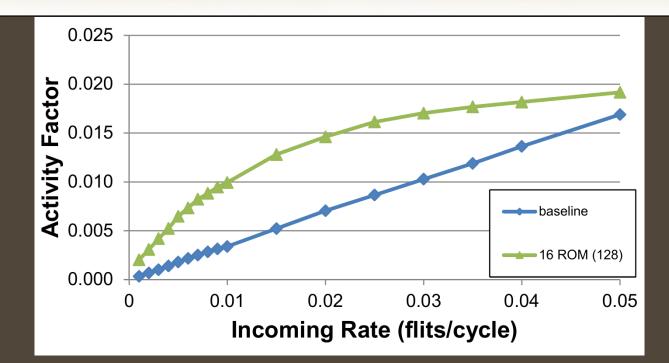
Lifetime improvement of *Use it or Lose it* router under PARSEC workloads normalized against baseline router.

- 10-65X increase in lifetime over baseline
 - Geo-mean of 22X improvement across benchmarks

Applications with routers that experience lowest minimum load see greatest gain

Results: Impact on Activity Factor



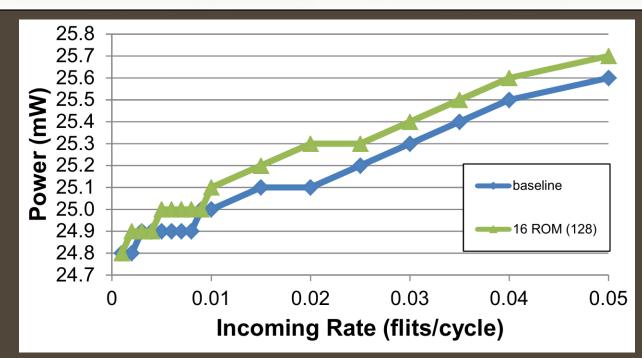


Activity factor for baseline and *Use it or Lose it* router under various incoming rate loads.

 Increase in activity factor only significant at low, < 0.05 flits/cycle, loads
 Little impact on HCI

Results: Impact on Power





Power consumption of baseline and *Use it or Lose it* router under various incoming rate loads.

• Maximum of < 1% increase in router power consumption





- Wearout is a growing problem in future CMOS technologies
 Over 10 years, 10x reliability improvement required
- Interconnect (NoC) critical point of failure in CMPs
- In the NoC, NBTI is dominant
 - Low activity of routers problematic
 - HCI less of an issue
- Introduced *Use it or Lose it* wear-resistant router microarchitecture
 - 22x improvement in lifetime
 - Insignificant overhead in energy or performance



Questions?